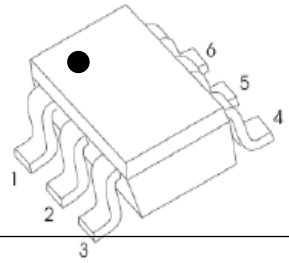
Plastic-Encapsulate MOSFETs

Dual P-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$MAX	I_D
-20V	520mΩ@-4.5V	-0.66A
	700mΩ@-2.5V	
	950mΩ(TYP)@-1.8V	

SOT-363



GENERRAL DESCRIPTION

This Dual P-Channel MOSFET has been designed using advanced Power Trench process to optimize the $R_{DS(ON)}$.

Including two P-ch CJ3139K MOSFET (independently) in a package.

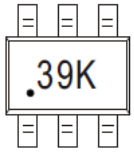
FEATURE

- High-Side Switching
- Low On-Resistance
- Low Threshold
- Fast Switching Speed

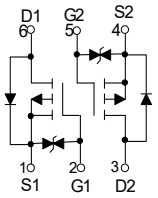
APPLICATION

- Drivers:Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

MARKING



Equivalent Circuit



Maximum ratings (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source voltage	V_{DSS}	-20	V
Typical Gate-Source Voltage	V_{GS}	±12	
Drain Current-Continuous	$I_{D(DC)}$	-0.66	A
Drain Current -Pulsed(note1)	$I_{DM(pulse)}$	-2.64	
Power Dissipation (note 2)	P_D	150	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	℃/W
Storage Temperature	T_j	150	℃
Junction Temperature	T_{stg}	-55 ~+150	

MOSFET ELECTRICAL CHARACTERISTICS

T_a=25℃ unless otherwise specified

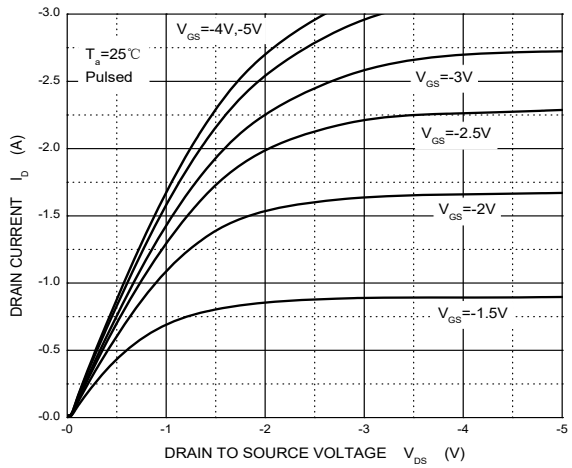
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
On/Off States						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =-250μA	-20			V
Gate-Threshold Voltage(note 3)	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA	-0.35	-0.45	-1.1	V
Gate-Body Leakage Current	I_{GSS}	V_{DS} =0V, V_{GS} =±10V			±20	μA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =-20V, V_{GS} =0V			-1	μA
Drain-Source On-State Resistance(note 3)	$R_{DS(on)}$	V_{GS} =-4.5V, I_D =-1A		430	520	mΩ
		V_{GS} =-2.5V, I_D =-800mA		624	700	mΩ
		V_{GS} =-1.8V, I_D =-500mA		950		mΩ
Forward Transconductance	g_{FS}	V_{DS} =-10V, I_D =-540mA	0.8			S
Dynamic Characteristics(note 4)						
Input Capacitance	C_{iss}	V_{DS} =-16V,V_{GS} =0V,f =1MHz			170	pF
Output Capacitance	C_{oss}				25	pF
Reverse Transfer Capacitance	C_{rss}				15	pF
Switching Times (note 4)						
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=-10V, I_D=-200mA, V_{GS}=-4.5V,R_G=10Ω		9		ns
Rise Time	t_r			5.8		ns
Turn-Off Delay Time	$t_{d(off)}$			32.7		ns
Fall Time	t_f			20.3		ns
Drain-Source Diode Characteristics						
Drain-Source Diode Forward Voltage (note 3)	V_{SD}	I_S=-0.5A, V_{GS} = 0V			-1.2	V

Notes:

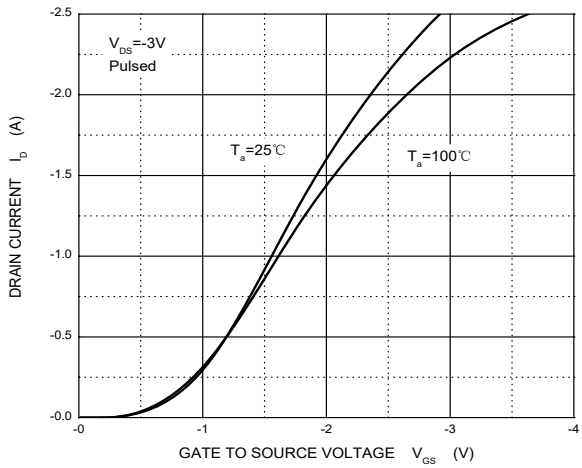
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. This test is performed with no heat sink at T_a=25℃.
3. Pulse Test : Pulse Width≤300μs, Duty Cycle≤0.5%.
4. These parameters have no way to verify.

Typical Characteristics

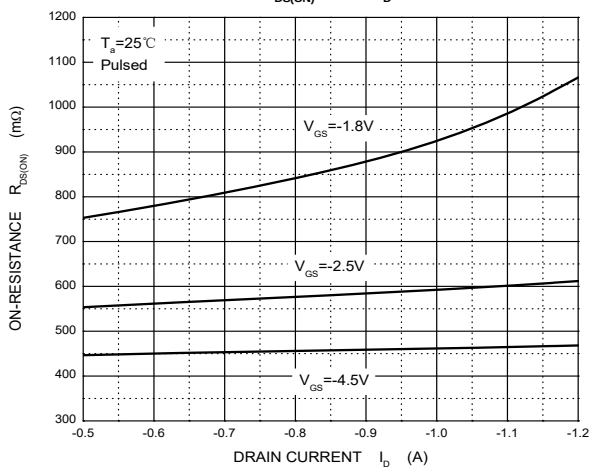
Output Characteristics



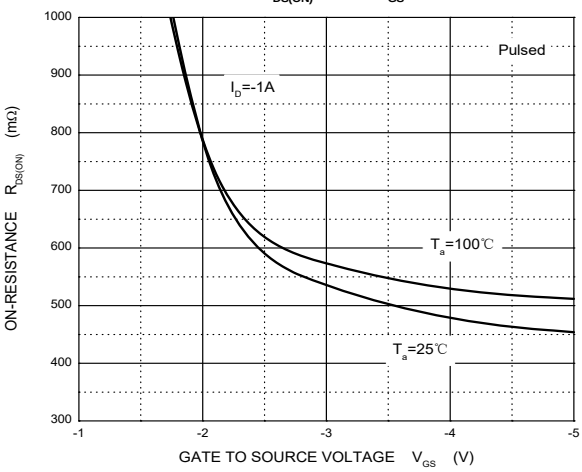
Transfer Characteristics



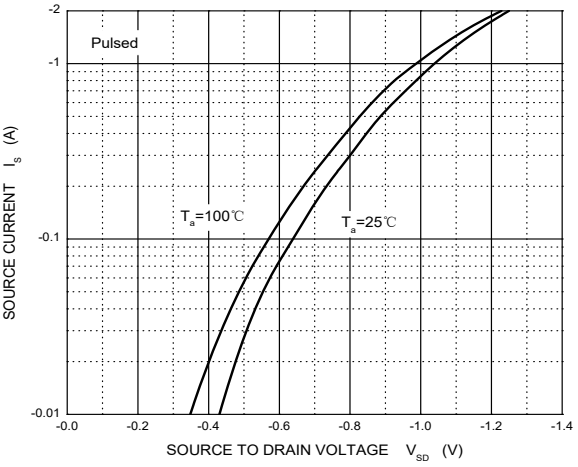
$R_{DS(ON)}$ —— I_D



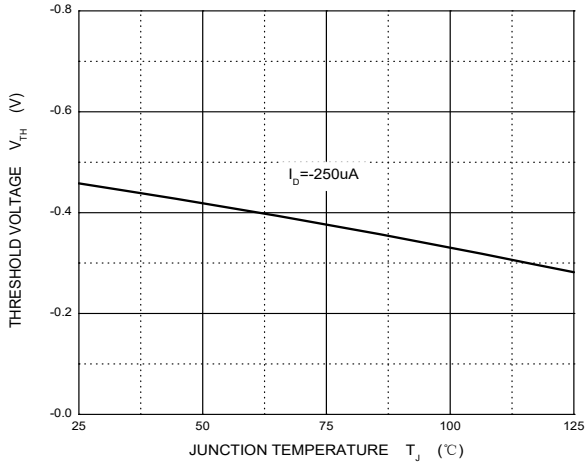
$R_{DS(ON)}$ —— V_{GS}



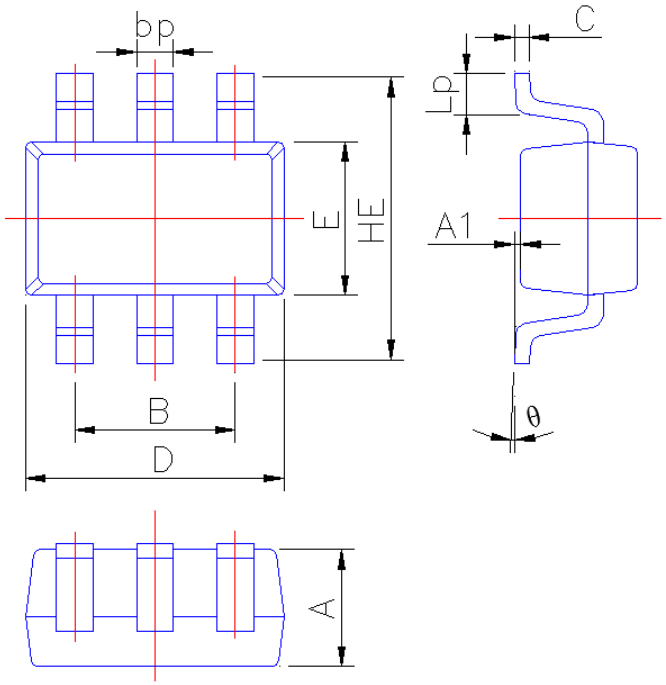
I_S —— V_{SD}



Threshold Voltage



SOT-363 Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
θ	0°	6°